

Type	Hits	Search Text	DBs	Time Stamp
1	BRS 348	semiconductor and dielectric and (hafnium adj oxide)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/21 11:33
2	BRS 141	(semiconductor and dielectric and (hafnium adj oxide) and (gate with dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/03/20 15:31
3	BRS 1358	257/405, 406, 410, 411.cc1s. or 438/216, 261, 288, 591.cc1s. (257/405, 406, 410, 411.cc1s. or 438/216, 261, 288, 591.cc1s.) and ((hafnium adj oxide) or HfO) (257/405, 406, 410, 411.cc1s. or 438/216, 261, 288, 591.cc1s.) and ((hafnium adj oxide) or HfO) and (dielectric with (layer or multilayer))	USPAT; US-PGPUB 11:35	2003/03/21 11:35
4	BRS 29		USPAT; US-PGPUB 11:36	2003/03/21 11:36
5	BRS 26		USPAT; US-PGPUB 11:37	2003/03/21 11:37